Ceramic Processing Research

New approach to provide an electrical conductivity to structural ceramics

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New approach to provide an electrical conductivity to insulator structural ceramics was suggested. In this concept, sintering additives form conductive network after sintering and result in a great reduction of amount of conductive phase addition compared with particle dispersion method generally used. Na^+ ionic-conductive silicon nitride and Na^+ ionic-conductive magnesia ceramics were successfully fabricated by this method.

Key words: Critical volume, Glassy Grain boundary phase, Ionic conductivity, Silicon nitride, Magnesia.

Introduction

To provide an electrical conductivity to insulator structural ceramics have been actively investigated to expand their applying area by replacement of electronic ceramics or metal products. It is also expected that high electrical conductivity brings them an improvement of machinability, which is one of the problems to be solved for structural ceramics, due to a probability to apply Electrical Discharge Machining (EDM) [1, 2]. In all attempts, conductive secondary phase "particles" were dispersed into the insulating matrix. Generally, TiN [3-6], SiC [7], and MoSi₂ [2] have been used as dispersed phases, where the electrical conductivity of composites increased according to percolation theory [8]. In the case of this method, massive addition, generally over 15 volume percent, is required to express enough conductivity, and it alters and governs the mechanical or physical properties of these ceramics. Here we will suggest the new approach to fabricate electrical-conductive structural ceramics by controlling the grain boundary phase with much less addition than particle dispersion method.

Theory

When conductive particles are dispersed into an insulator matrix and volume of the conductive phase increases from zero up to a critical volume fraction of percolation, one particle contact with neighbors and form finite conductive path in grain boundary, where entire composite is insulating. Near the critical volume, infinite conductive network is formed and the resistivity of the entire composite abruptly decreases (insulator-conductor transition). To reduce the volume of dispersed phase, an approach by controlling the size of dispersed particles have been generally adopted. It is computationally and experimentally reported that the critical volume fraction changed according to the ratio between a radius of dispersed phased R_m and matrix particles R_p [9, 10]. R. P. Kusy [10] described the critical volume fraction V_c for conductive phase in terms of the particle size ratio as

$$N = N' + N''$$

$$V_{c} = \frac{1 + (N''/N')}{1 + (N''/N') + (1/N')(R_{n}/R_{m})^{3}}$$

where N, N' and N'' are total number of dispersed particles, number of particles, which contribute to and which are redundant to forming conductive network, respectively. This indicates that the critical volume fraction of secondary phase can be decreased to a several percent by reducing the size of dispersed particles for constant size of matrix grains as illustrated in Fig. 1(a) and (b). However, at least about 10 vol% of addition was required due to experimental limitation for ceramic composites or nanocomposites until today.

In this research, we focused on grain boundary of ceramic materials, which can be considered as infinite network. Some of structural ceramics fabricated with sintering additives have residual grain boundary phases, which consist of glassy or crystalline phase. By controlling the composition of grain boundary phase to form electrical-conductive glassy grain boundary phase

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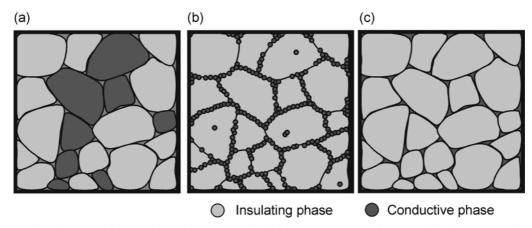


Fig. 1. Illustrations describing an influence of particle size ratio and a difference between conductive particle dispersion and conductive grain boundary phase. (a) Large size conductive particles are dispersed in insulator matrix ($R_m \approx R_{p.}$) (b) Small particles are dispersed ($R_m \leq R_{p.}$) (c) Conductive grain boundary phase is formed.

as shown in Fig. 1(c), it is certainly expected that the radius of conductive phase R_m can be reduced into near zero, resulting in an abrupt decrease of critical volume V_c , since the glassy phase is not aggregation of "particles." In this concept, only sintering additives, which forms conductive glassy grain boundary phase after sintering, are required instead of conductive particles.

Experimental

Very fine α -Si₃N₄ (SN-E10, Ube Industries Co., Ltd., Ube, Japan) and MgO powder (500A, Ube Material Industry Ltd., Ube, Japan) with high purity were used as matrices. Na₂O-Al₂O₃-SiO₂ glass, which is known as Na⁺-ion conductive glass [11, 12], was selected both to form liquid phase as sintering aids and to easily vitrify in Si₃N₄ and MgO ceramics. α-Al₂O₃ (>99.99% pure, Taimicron TM-DAR, Taimei Chemicals Co. Ltd., Nagano, Japan), Na₂CO₃ (>99% pure, KOJUNDO Chemical Laboratory, Saitama, Japan), which is a source of Na₂O, and SiO₂ (>99.9% pure, KOJUNDO Chemical Laboratory, Saitama, Japan) were used as sintering additives. These components were weight into a composition 90 Si₃N₄ (or MgO)/10 (40 Na₂O - 30 Al₂O₃ - 30 SiO₂ [mol%]) [wt%]. They were mixed by wet ball-milling in a polyethylene pot with ethanol for 24 hours. Then, the mixed powders were dried and crushed by dry ball-milling in the polyethylene pot for 24 hours to eliminate the agglomerates. These powders were packed into carbon mold with 20 mm in insidediameter and sintered by a Pulsed Electric Current Sintering (PECS) (Dr. SINTER[™], SPS-2040, IZUMI TECHNOLOGY Co., Ltd., Hokkaido, Japan). The Si₃N₄ ceramics were sintered at 1600°C for 3 minutes under an applied pressure of 50 MPa in N₂ atmosphere. The MgO ceramics were sintered at 1300°C for 3 minutes under 30 MPa in Ar. The heating rate for all sintering was 100°C/min. As-sintered samples were ground by diamond wheels and polished with diamond pastes to less than 1 mm in thickness.

Crystalline phases of sintered specimens were determined by XRD analysis.

The electrical conductivity was calculated from the resistance measured by two-terminal A.C. method between 100 and 1000°C at frequency of 10 kHz in air atmosphere by using LCR meter (HP-4284A, Hewlett Packard Co., USA). Before the measuring, platinum electrodes were pasted at the center of both side of specimens with 15 mm diameter and heat-treated at 700°C for 1 minute.

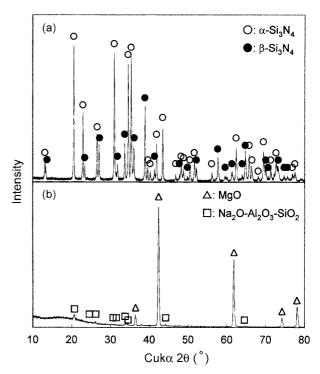


Fig. 2. XRD data for (a) $Si_3N_4/Na_2O-Al_2O_3-SiO_2$ ceramics with 87: 13 of α : β phase ratio and (b) MgO/Na_2O-Al_2O_3-SiO_2 ceramics.

Specimen $\overline{Si_{3}N_{4}/Na_{2}O-Al_{2}O_{3}-SiO_{2}}$ $Si_{3}N_{4}/Y_{2}O_{3}-Al_{2}O_{3}^{a)}$	Electrical conductivity $[S \cdot cm^{-1}]$		Activation anarry [[s]mal ⁻¹]	
	100°C	1000°C	- Activation energy [kJmol ⁻¹]	
	$2.6 imes 10^{-8}$ $3.3 imes 10^{-10}$	3.5×10^{-3} 2.2×10^{-7}	57.2 (100-1000°C) 21.4 (100-575°C)	81.6 (575-1000°C)
MgO/Na ₂ O-Al ₂ O ₃ -SiO ₂ MgO	1.7×10^{-7} _b)	1.8×10^{-3} 8.2×10^{-7}	46.0 (100-1000°C) 70.1 (350-1000) ^{c)}	

Table 1. Parameters describing the electrical conductivities.

^{a)}91Si₃N₄/6Y₂O₃-3Al₂O₃ [mol%]

^{b)}An electrical conductivity at 100°C for MgO couldnít measure, since the conductivity was out of a measurement range of HP-4284A.

^{c)}Only one value was calculated for MgO, because it was difficult to decide whether the variation of electrical conductivity has flexion point or not.

Results and Discussions

Sufficiently densed materials are successfully fabricated by PECS for both Si₃N₄ and MgO ceramics. From XRD result for Si₃N₄ ceramics, only α - and β -Si₃N₄ were identified and no crystalline phase in grain boundary was determined as shown in Fig. 2(a). A broad bulge in the lower 20 angle area of XRD data for MgO ceramics (see Fig. 2(b)) obviously indicates an existence of glassy grain boundary phase. In the case of MgO ceramics, some extent of glassy phase crystallized to Na₂O-Al₂O₃-SiO₂. It can be thought that a fast cooling of the PECS assisted to form these glassy grain boundary phases. The presences of ionic-conductive grain boundary phase in the Si₃N₄/Na₂O-Al₂O₃-SiO₂ ceramics confirmed by Transmission Electron were also Microscope (TEM) with Energy Dispersive X-ray Spectroscopy (EDS) [13].

The electrical conductivity and activation energy for both ceramics were indicated in Table 1. The data for Si₃N₄/Al₂O₃-Y₂O₃ and monolithic MgO were also listed for comparison. The values for Si₃N₄/Na₂O-Al₂O₃-SiO₂ ceramics were two orders of magnitude higher at 100°C and four orders of magnitude higher at 1000°C than those of Si₃N₄/Y₂O₃-Al₂O₃, respectively. And that for MgO/Na₂O-Al₂O₃-SiO₂ was about three orders of magnitude higher than monolithic MgO at 1000°C. This dramatic improvement suggests that the Na₂O-Al₂O-SiO₂ glassy phases were constructed as their grain boundary phases and Na⁺ cation could carry charge through the glass network [13, 14]. In the variation of electrical conductivity for Si₃N₄/Y₂O₃-Al₂O₃ ceramics, activation energy in high temperature range was higher than that in low temperature range as well as the former report by Ohno, et al. [15]. On the other hand, the Si₃N₄ and MgO ceramics with Na₂O-Al₂O₃-SiO₂ additives showed no flexion point in the variation of conductivity, similarly to the Na₂O₃-Al₂O₃-SiO₂ glass [11]. The similarity of variation and values between these ceramics and pure glass clearly indicates that electrical properties of glassy phases, which formed in grain boundary, dominates those of entire materials fabricated by this method.

Summary

The Si_3N_4 and the MgO ceramics with Na^+ -ionic conductivity were successfully fabricated by controlling the composition of grain boundary phase. They showed much higher electrical conductivity compared with conventional Si_3N_4 and MgO ceramics. The advantage of this concept is a facility of the processing and that much lower addition is required to express the electric conductivity than the particle dispersion method.

As Si_3N_4 ceramic is generally sintered by using oxide additives due to its low sinterability and has residual glassy phase in the grain boundary, it was expected that it is relatively easy to form ionic-conductive glassy phase as the grain boundary. On the other hand, MgO ceramic can be easily fabricated without additives. The present result for MgO/Na₂O-Al₂O₃-SiO₂ ceramics indicates certain possibility that this concept can be applied to a number of matrices whether the matrices require sintering additives or not.

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